

isc Silicon PNP Power Transistor

2SB720

DESCRIPTION

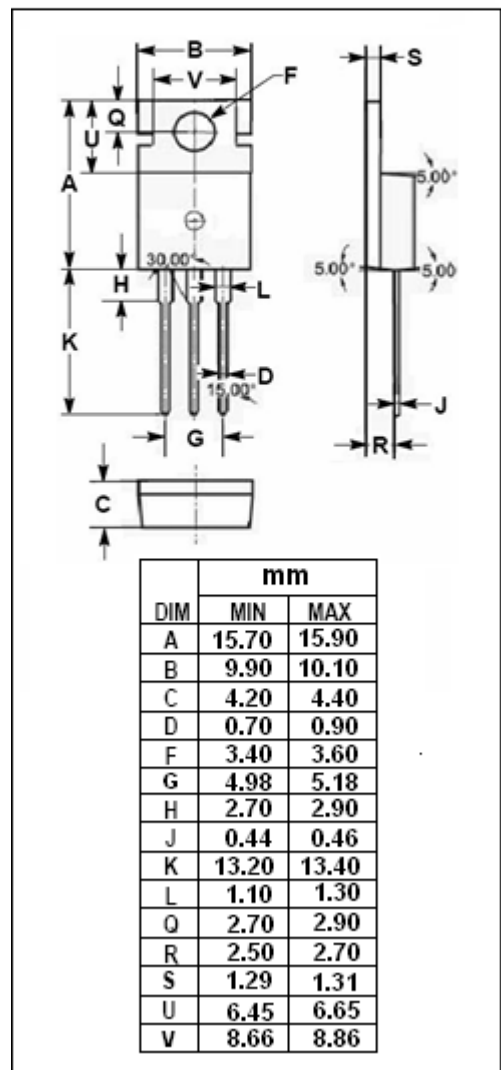
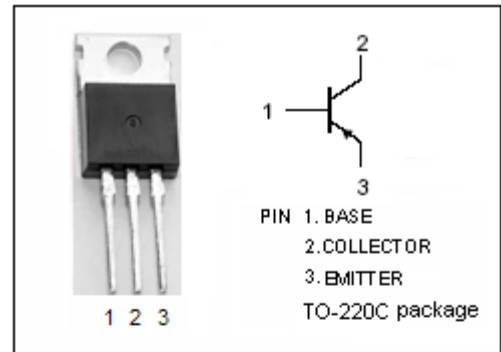
- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -200V(\text{Min})$
- Wide Area of Safe Operation
- Complement to Type 2SD760

APPLICATIONS

- Designed for power amplifier and TV vertical deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-200	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-3	A
P_C	Total Power Dissipation@ $T_C=25^\circ\text{C}$	25	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor**2SB720****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -5\text{mA}; I_B = 0$	-200			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -0.1\text{mA}; I_E = 0$	-200			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -0.1\text{mA}; I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -500\text{mA}; I_B = -50\text{mA}$			-1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -500\text{mA}; I_B = -50\text{mA}$			-1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -200\text{V}; I_E = 0$			-10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -3.0\text{V}; I_C = 0$			-10	μA
h_{FE}	DC Current Gain	$I_C = -150\text{mA}; V_{CE} = -5\text{V}$	35		200	
f_T	Current-Gain—Bandwidth Product	$I_C = -100\text{mA}; V_{CE} = -10\text{V}$		100		MHz

◆ **h_{FE} Classifications**

A	B	C
35-70	60-120	100-200